

isc N-Channel MOSFET Transistor

IRFB4710, IIRFB4710

FEATURES

- Static drain-source on-resistance:
 R_{DS}(on) ≤0.014Ω
- Enhancement mode
- · Fast Switching Speed
- · 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

DESCRITION

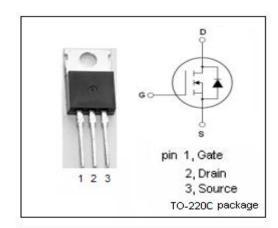
• reliable device for use in a wide variety of applications

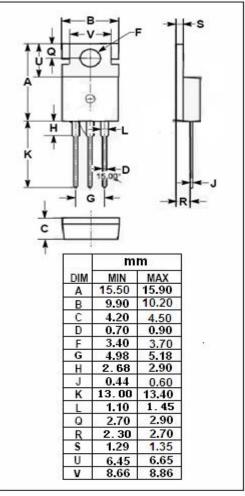
• ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

ABOOLOTE INACIMONI (ATINOO(1a 200)							
SYMBOL	PARAMETER	VALUE	UNIT				
V _{DSS}	Drain-Source Voltage	100	V				
V _{GS}	Gate-Source Voltage	±20	V				
I _D	Drain Current-Continuous	75	А				
I _{DM}	Drain Current-Single Pulsed	300	А				
P _D	Total Dissipation @T _C =25°C	200	W				
Tj	Max. Operating Junction Temperature	175	$^{\circ}$				
T _{stg}	Storage Temperature	-55~175	°C				

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
Rth(ch-c)	Channel-to-case thermal resistance	0.74	°C/W
Rth(ch-a)	Rth(ch-a) Channel-to-ambient thermal resistance		°C/W







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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	MAX	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; ID =250 μ A	100			V
$V_{\text{GS(th)}}$	Gate Threshold Voltage	V _{DS} =V _{GS} ; ID =250 μ A	3.5		5.5	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =10V; I _D =45A			0.014	Ω
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V			±0.1	μ А
I _{DSS}	Drain-Source Leakage Current	V _{DS} =95V; V _{GS} = 0V			1.0	μА
V_{SD}	Diode forward voltage	Is=45A, V _{GS} = 0V			1.3	V

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